

Introduction to CMOS VLSI Design

Lecture 20: Package, Power, and I/O

Outline

- ☐ Packaging
- ☐ Power Distribution
- ☐ I/O
- ☐ Synchronization

Packages

□ Package functions

- Electrical connection of signals and power from chip to board
- Little delay or distortion
- Mechanical connection of chip to board
- Removes heat produced on chip
- Protects chip from mechanical damage
- Compatible with thermal expansion
- Inexpensive to manufacture and test

TSOP : Thin Small Outline Package

PLCC : Plastic Leaded Chip Carrier

BGA : Ball Grid array

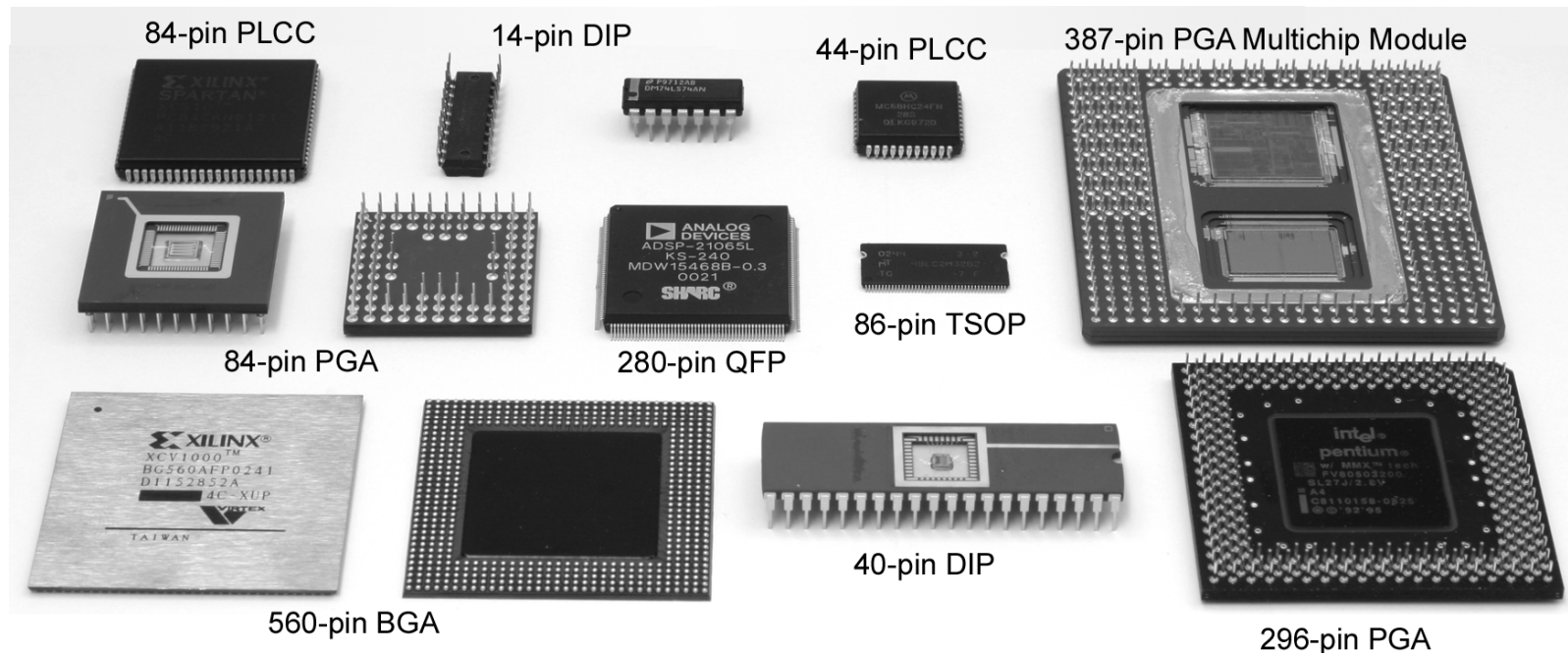
DIP : Dual In-line Package

PGA : Pin Grid Array

QFP : Quad Flat Pack

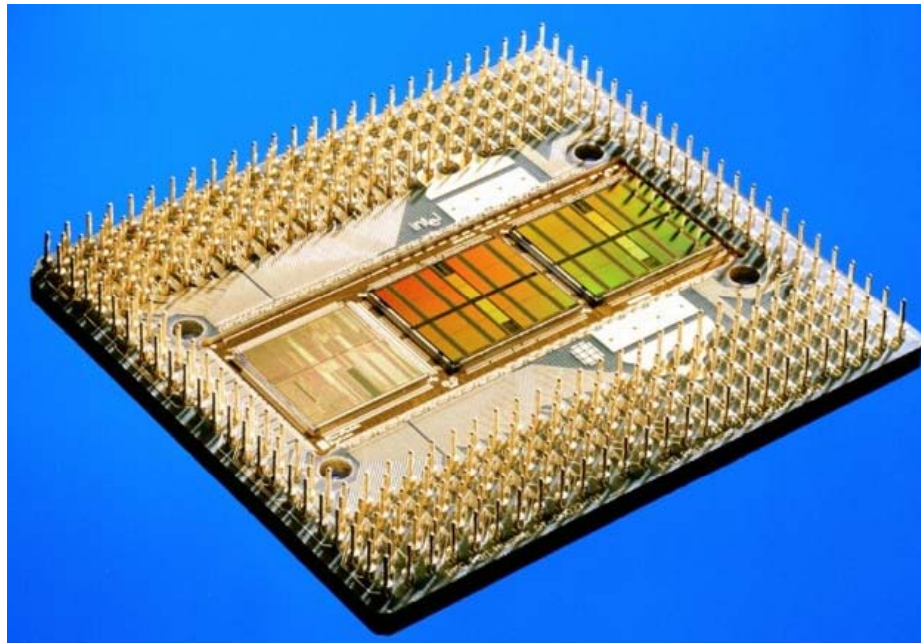
Package Types

□ Through-hole vs. surface mount



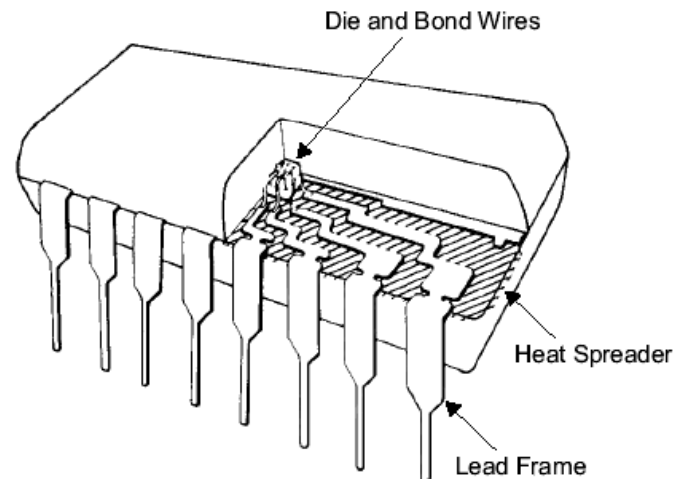
Multichip Modules

- ❑ Pentium Pro MCM (Multi Chip Module)
 - Fast connection of CPU to cache
 - Expensive, requires known good dice



Chip-to-Package Bonding

- ❑ Traditionally, chip is surrounded by *pad frame*
 - Metal pads on 100 – 200 μm pitch
 - Gold *bond wires* attach pads to package
 - *Lead frame* distributes signals in package
 - Metal *heat spreader* helps with cooling

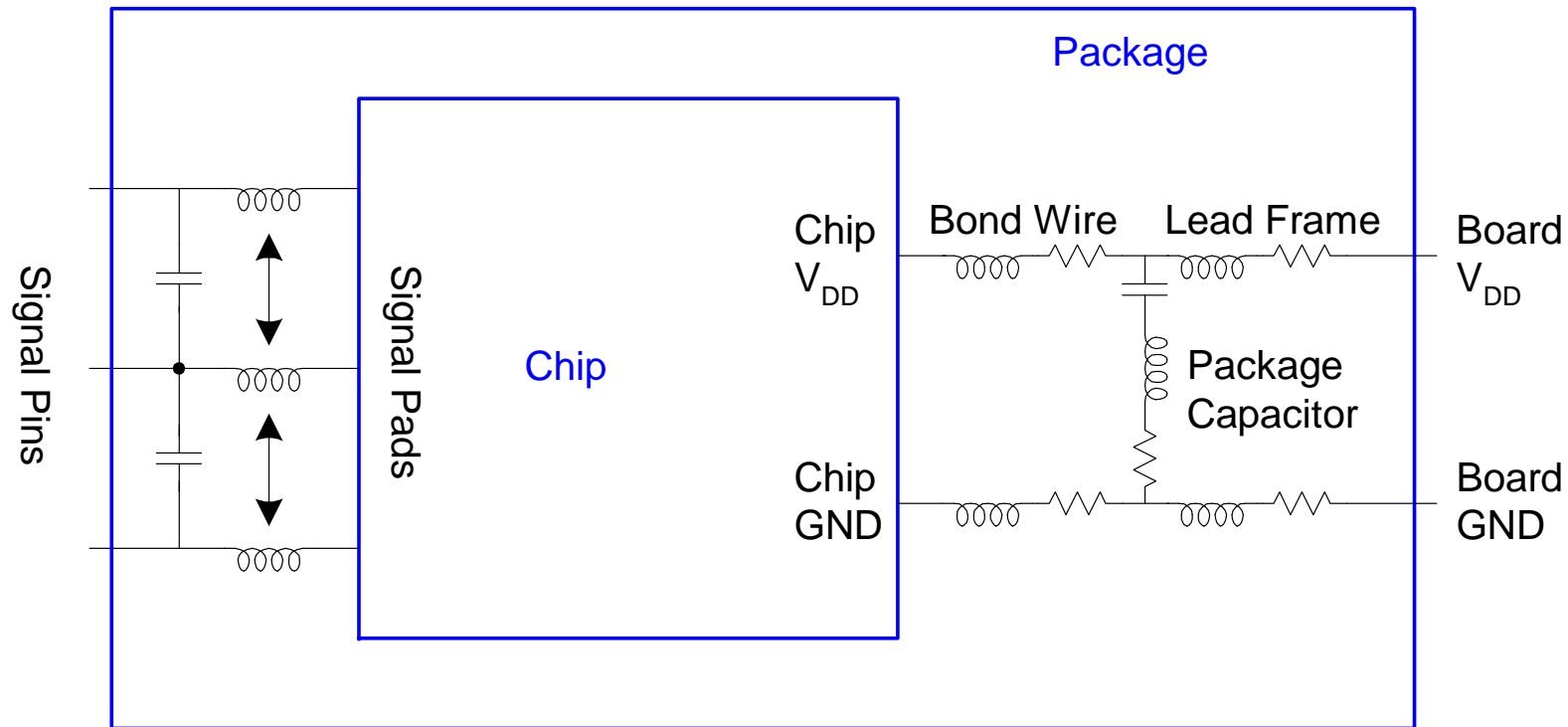


Advanced Packages

- ❑ Bond wires contribute parasitic inductance
- ❑ Fancy packages have many signal, power layers
 - Like tiny printed circuit boards
- ❑ *Flip-chip* places connections across surface of die rather than around periphery
 - Top level metal pads covered with solder balls
 - Chip flips upside down
 - Carefully aligned to package (done blind!)
 - Heated to melt balls
 - Also called *C4* (Controlled Collapse Chip Connection)

Package Parasitics

- ❑ Use many V_{DD} , GND in parallel
 - Inductance, I_{DD}



Heat Dissipation

- ❑ 60 W light bulb has surface area of 120 cm²
- ❑ Itanium 2 die dissipates 130 W over 4 cm²
 - Chips have enormous power densities
 - Cooling is a serious challenge
- ❑ Package spreads heat to larger surface area
 - Heat sinks may increase surface area further
 - Fans increase airflow rate over surface area
 - Liquid cooling used in extreme cases (\$\$\$)

Thermal Resistance

- ❑ $\Delta T = \theta_{ja} P$
 - ΔT : temperature rise on chip
 - θ_{ja} : thermal resistance of chip junction to ambient
 - P : power dissipation on chip
- ❑ Thermal resistances combine like resistors
 - Series and parallel
- ❑ $\theta_{ja} = \theta_{jp} + \theta_{pa}$
 - Series combination

Example

- ❑ Your chip has a heat sink with a thermal resistance to the package of 4.0°C/W .
- ❑ The resistance from chip to package is 1°C/W .
- ❑ The system box ambient temperature may reach 55°C .
- ❑ The chip temperature must not exceed 100°C .
- ❑ What is the maximum chip power dissipation?

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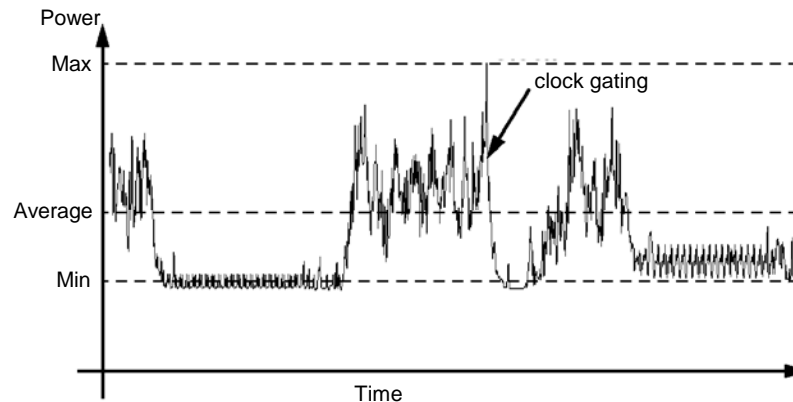
- ❑ $(100 - 55 \text{ C}) / (4 + 1 \text{ C/W}) = 9 \text{ W}$

Power Distribution

- ❑ Power Distribution Network function (through power lines)
 - Carry current from pads to transistors on chip
 - Maintain stable voltage with low noise
 - Provide average and peak power demands
 - Provide current return paths for signals
 - Avoid electromigration & self-heating wearout
 - Consume little chip area and wire
 - Easy to lay out

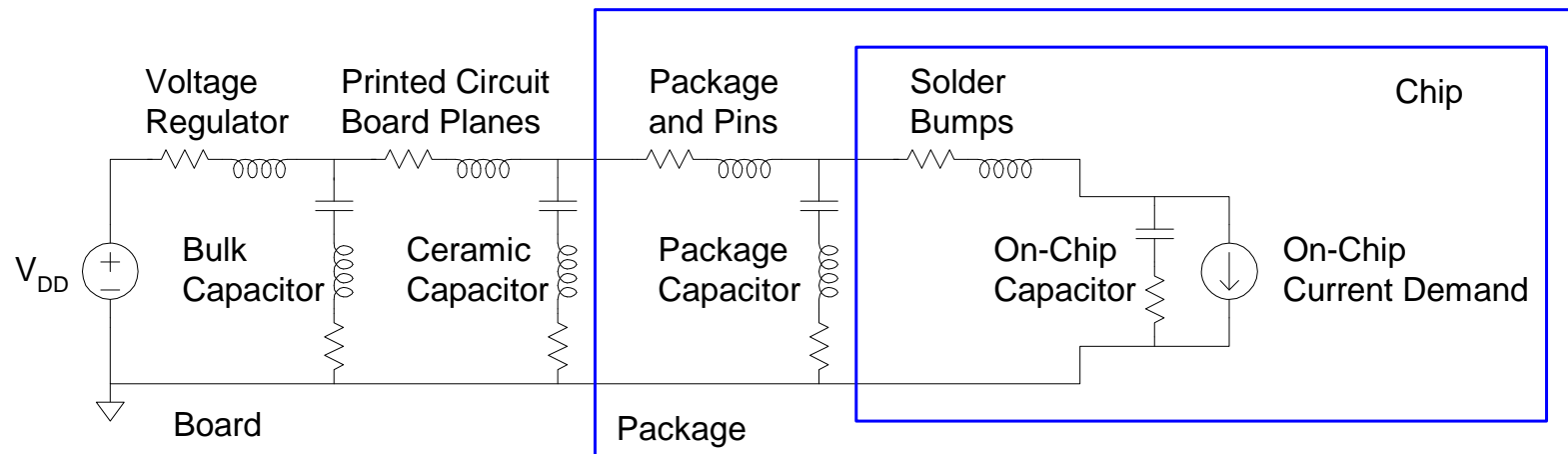
Power Requirements

- ❑ $V_{DD} = V_{DDnominal} - V_{droop}$
- ❑ Want $V_{droop} < \pm 10\%$ of V_{DD}
- ❑ Sources of V_{droop}
 - IR drops
 - $L di/dt$ noise
- ❑ I_{DD} changes on many time scales



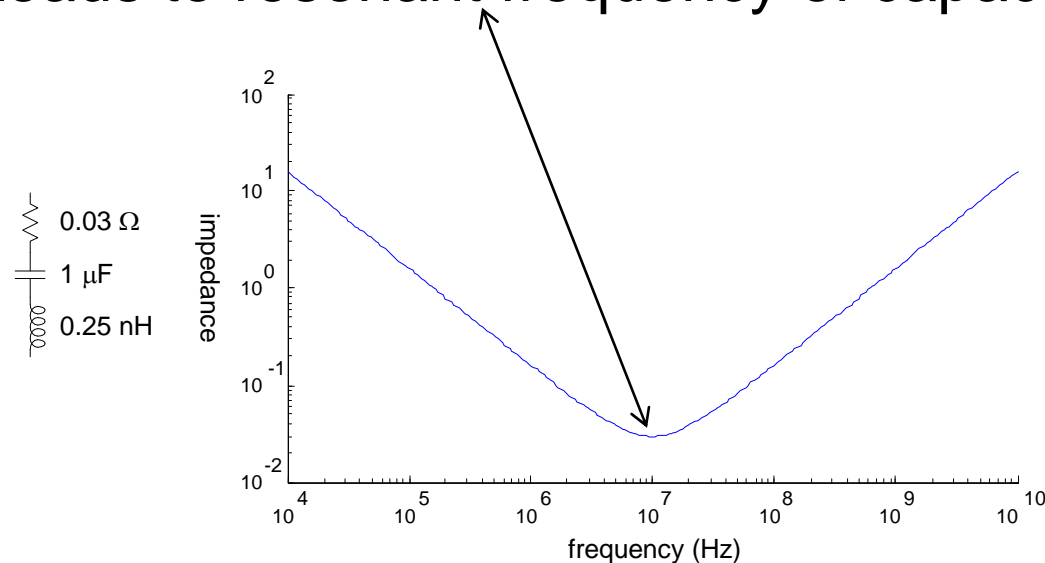
Power System Model

- ❑ Power comes from regulator on system board
 - Board and package add parasitic R and L
 - Bypass capacitors help stabilize supply voltage
 - But capacitors also have parasitic R and L
- ❑ Simulate system for time and frequency responses



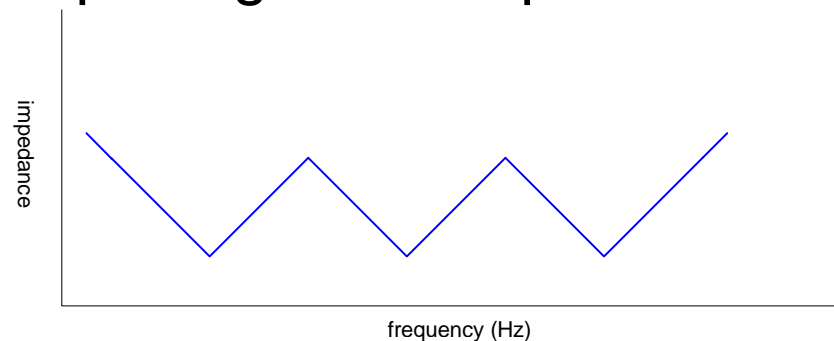
Bypass Capacitors

- ❑ Need low supply impedance at all frequencies
- ❑ Ideal capacitors have impedance decreasing with ω
- ❑ Real capacitors have parasitic R and L
 - Leads to resonant frequency of capacitor



Frequency Response

- ❑ Use multiple capacitors in parallel
 - Large capacitor near regulator has low impedance at low frequencies
 - But also has a low self-resonant frequency
 - Small capacitors near chip and on chip have low impedance at high frequencies
- ❑ Choose caps to get low impedance at all frequencies



Input / Output

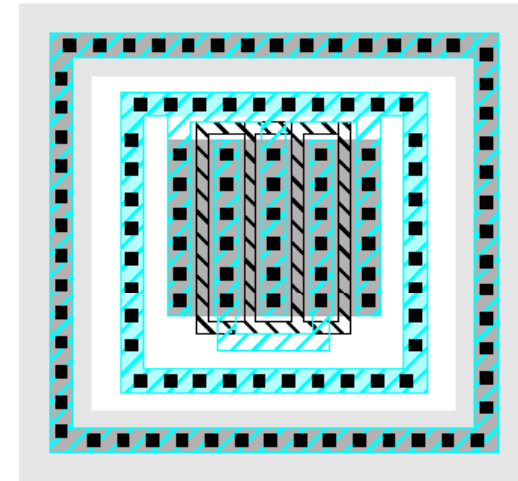
- ❑ Input/Output System functions
 - Communicate between chip and external world
 - Drive large capacitance off chip
 - Operate at compatible voltage levels
 - Provide adequate bandwidth
 - Limit slew rates to control di/dt noise
 - Protect chip against electrostatic discharge
 - Use small number of pins (low cost)

I/O Pad Design

- ❑ Pad types
 - V_{DD} / GND
 - Output
 - Input
 - Bidirectional
 - Analog

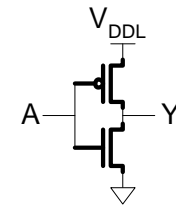
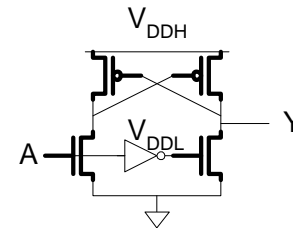
Output Pads

- ❑ Drive large off-chip loads (2 – 50 pF)
 - With suitable rise/fall times
 - Requires chain of successively larger buffers
- ❑ Guard rings to protect against latchup
 - Noise below GND injects charge into substrate
 - Large nMOS output transistor
 - p+ inner guard ring
 - n+ outer guard ring
 - In n-well

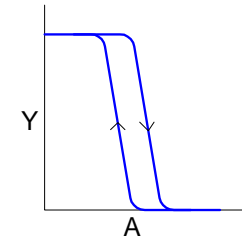
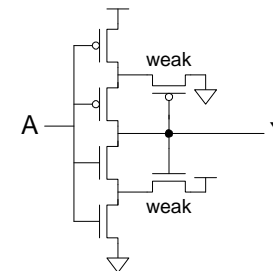


Input Pads

- ❑ Level conversion
 - Higher or lower off-chip V
 - May need thick oxide gates



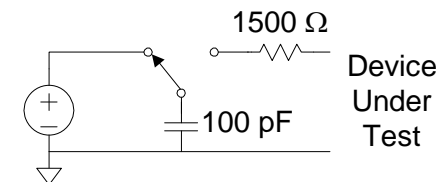
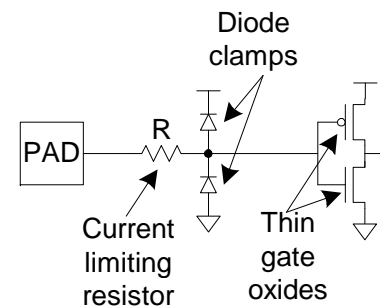
- ❑ Noise filtering
 - Schmitt trigger
 - Hysteresis changes V_{IH} , V_{IL}



- ❑ Protection against electrostatic discharge

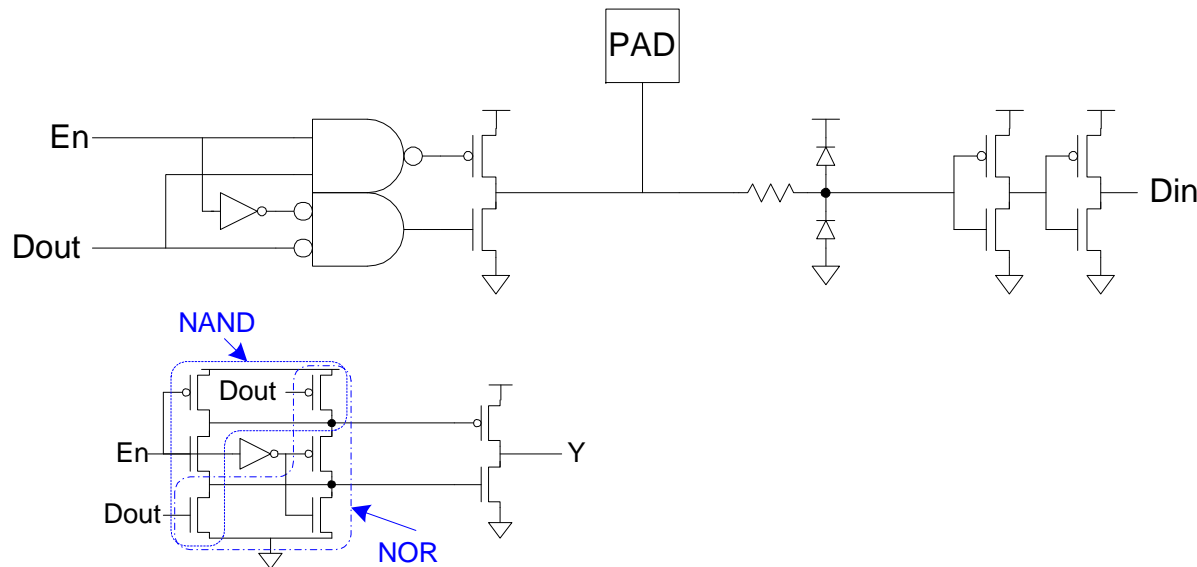
ESD Protection

- ❑ Static electricity builds up on your body
 - Shock delivered to a chip can fry thin gates
 - Must dissipate this energy in protection circuits before it reaches the gates
- ❑ ESD protection circuits
 - Current limiting resistor
 - Diode clamps
- ❑ ESD testing
 - Human body model
 - Views human as charged capacitor



Bidirectional Pads

- ❑ Combine input and output pad
- ❑ Need tristate driver on output
 - Use enable signal to set direction
 - Optimized tristate avoids huge series transistors



Analog Pads

- ❑ Pass analog voltages directly in or out of chip
 - No buffering
 - Protection circuits must not distort voltages

MOSIS I/O Pad

- ❑ 1.6 μm two-metal process
 - Protection resistors
 - Protection diodes
 - Guard rings
 - Field oxide clamps

